



Form 1449\*

Atty. Docket No.: 303.557US1

Serial No. 09/259,849

INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

Applicant: Paul A. Farrar

(Use several sheets if necessary)

Filing Date: March 1, 1999

Group: 1765

## U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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<i>JP</i>	4,386,116	05/31/1983	Nair, et al.	427	99	12/24/81
<i>JP</i>	4,423,547	01/03/1984	Farrar, P.A., et al.	29	571	06/01/81
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5/30/01

\*Substitute Disclosure Statement Form (P10-0449)

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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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*James H. Parilla*

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*Guillermo Peralta*

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